METHOD FOR FORMING PI-TYPE ASSISTANT ELECTRODE

Abstract

The present invention provides a method for improving the adhesion capability between the π -type bus electrode and ITO (indium tin oxide) transparent conductive layer. The method includes an ITO transparent conductive layer as an ITO electrode is formed on the glass substrate by sputtering method. Then, a photoresist layer with a cavity pattern is formed on the portion of the ITO transparent conductive film. Next, an etching process is used to remove portion of the ITO transparent conductive film to form a cavity within the ITO transparent conductive film. Then, after removing the photoresist layer, a silver paste as a bus electrode is formed on the glass substrate and on the ITO transparent conductor film to form a pi (π) type bus electrode by print method. Due to the pi side of the pi-type electrode is formed on the cavity thereby the adhesion capability between the pi-type bus electrode and exposed glass substrate within the cavity, such that the adhesion capability between the π type bus electrode and ITO conductive film can be improved. Thus, the edge warp phenomenon of the π type bus electrode can be diminished.